

DATA SHEET

TEA1062; TEA1062A Low voltage transmission circuits with dialler interface

Product specification
Supersedes data of 1996 Dec 04
File under Integrated Circuits, IC03

1997 Sep 03

Low voltage transmission circuits with dialler interface

TEA1062; TEA1062A

FEATURES

- Low DC line voltage; operates down to 1.6 V (excluding polarity guard)
- Voltage regulator with adjustable static resistance
- Provides a supply for external circuits
- Symmetrical high-impedance inputs (64 k Ω) for dynamic, magnetic or piezoelectric microphones
- Asymmetrical high-impedance input (32 k Ω) for electret microphones
- DTMF signal input with confidence tone
- Mute input for pulse or DTMF dialling
 - TEA1062: active HIGH (MUTE)
 - TEA1062A: active LOW ($\overline{\text{MUTE}}$)
- Receiving amplifier for dynamic, magnetic or piezoelectric earpieces
- Large gain setting ranges on microphone and earpiece amplifiers
- Line loss compensation (line current dependent) for microphone and earpiece amplifiers
- Gain control curve adaptable to exchange supply
- DC line voltage adjustment facility.

GENERAL DESCRIPTION

The TEA1062 and TEA1062A are integrated circuits that perform all speech and line interface functions required in fully electronic telephone sets. They perform electronic switching between dialling and speech. The ICs operate at line voltage down to 1.6 V DC (with reduced performance) to facilitate the use of more telephone sets connected in parallel.

All statements and values refer to all versions unless otherwise specified.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{LN}	line voltage	$I_{line} = 15 \text{ mA}$	3.55	4.0	4.25	V
I_{line}	operating line current		11	–	140	mA
	normal operation		1	–	11	mA
	with reduced performance					
I_{CC}	internal supply current	$V_{CC} = 2.8 \text{ V}$	–	0.9	1.35	mA
V_{CC}	supply voltage for peripherals	$I_{line} = 15 \text{ mA}$				
	TEA1062	$I_p = 1.2 \text{ mA}$; MUTE = HIGH	2.2	2.7	–	V
		$I_p = 0 \text{ mA}$; MUTE = HIGH	–	3.4	–	V
	TEA1062A	$I_p = 1.2 \text{ mA}$; $\overline{\text{MUTE}}$ = LOW	2.2	2.7	–	V
		$I_p = 0 \text{ mA}$; $\overline{\text{MUTE}}$ = LOW	–	3.4	–	V
G_v	voltage gain					
	microphone amplifier		44	–	52	dB
	receiving amplifier		20	–	31	dB
T_{amb}	operating ambient temperature		–25	–	+75	°C
Line loss compensation						
ΔG_v	gain control		–	5.8	–	dB
V_{exch}	exchange supply voltage		36	–	60	V
R_{exch}	exchange feeding bridge resistance		0.4	–	1	k Ω

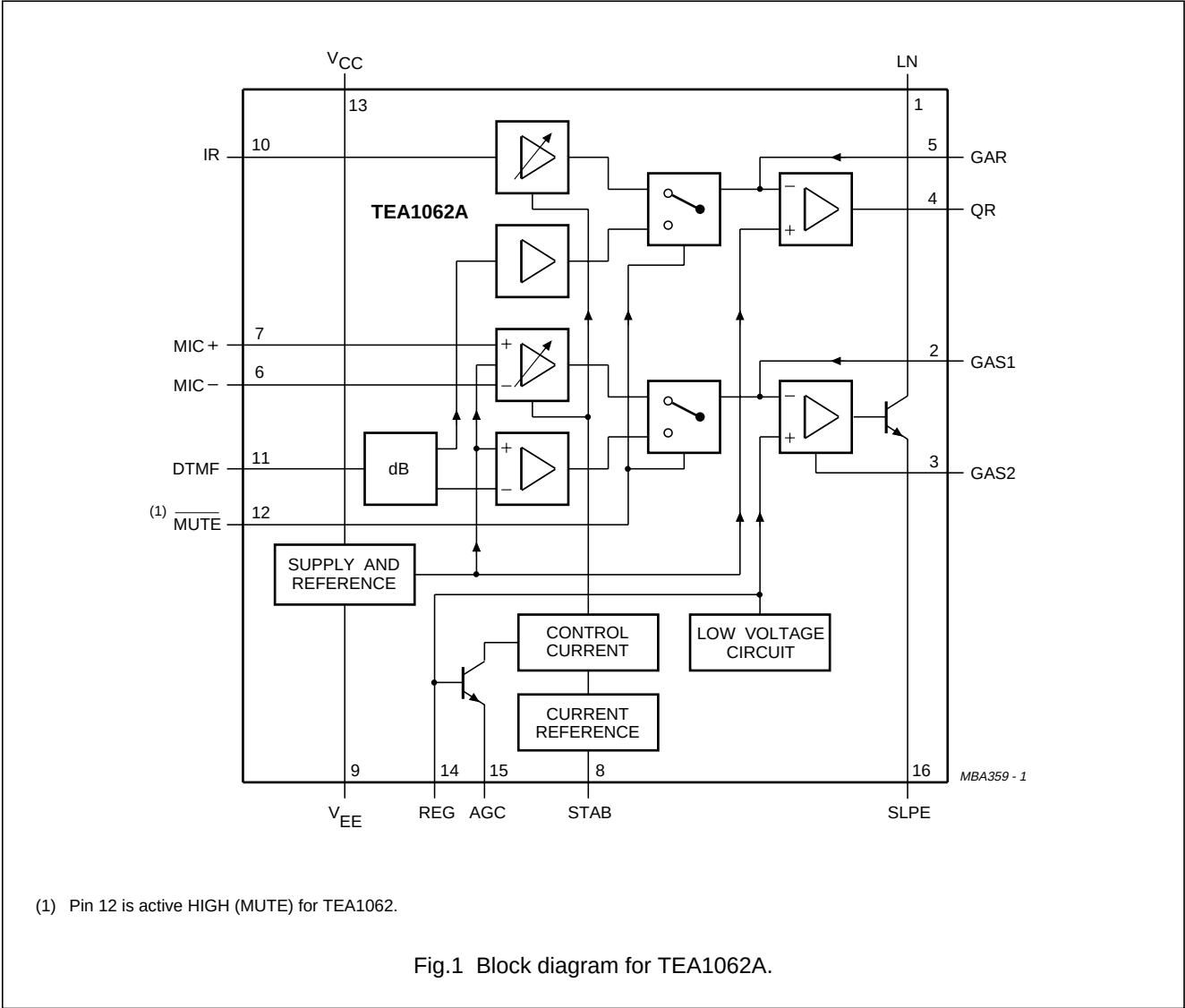
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ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
TEA1062	DIP16	plastic dual in-line package; 16 leads (300 mil)	SOT38-1
TEA1062M1	DIP16	plastic dual in-line package; 16 leads (300 mil)	SOT38-4 or SOT38-9
TEA1062A	DIP16	plastic dual in-line package; 16 leads (300 mil)	SOT38-1
TEA1062AM1	DIP16	plastic dual in-line package; 16 leads (300 mil)	SOT38-4 or SOT38-9
TEA1062T	SO16	plastic small outline package; 16 leads; body width 3.9 mm	SOT109-1
TEA1062AT	SO16	plastic small outline package; 16 leads; body width 3.9 mm	SOT109-1

BLOCK DIAGRAM



Low voltage transmission circuits with dialler interface

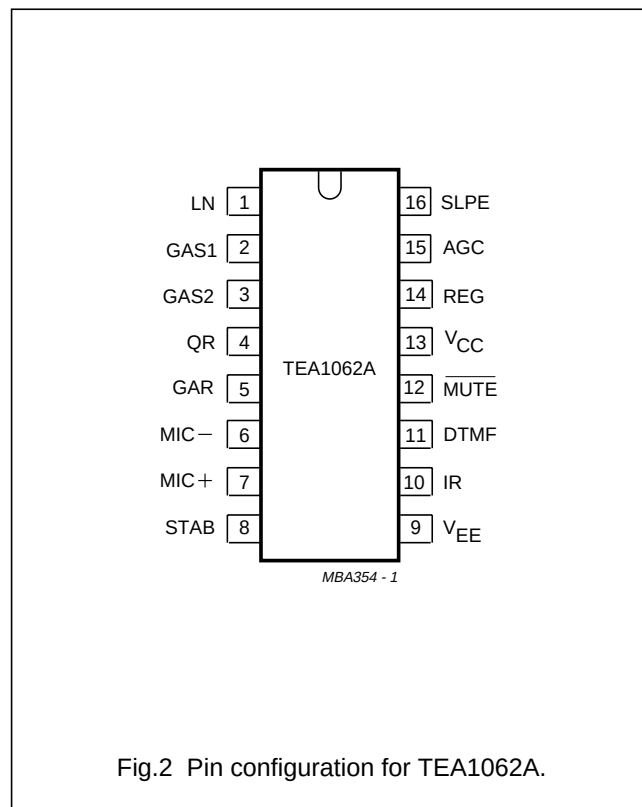
TEA1062; TEA1062A

PINNING

SYMBOL	PIN	DESCRIPTION
LN	1	positive line terminal
GAS1	2	gain adjustment; transmitting amplifier
GAS2	3	gain adjustment; transmitting amplifier
QR	4	non-inverting output; receiving amplifier
GAR	5	gain adjustment; receiving amplifier
MIC-	6	inverting microphone input
MIC+	7	non-inverting microphone input
STAB	8	current stabilizer
V _{EE}	9	negative line terminal
IR	10	receiving amplifier input
DTMF	11	dual-tone multi-frequency input
MUTE	12	mute input (see note 1)
V _{CC}	13	positive supply decoupling
REG	14	voltage regulator decoupling
AGC	15	automatic gain control input
SLPE	16	slope (DC resistance) adjustment

Note

- Pin 12 is active HIGH (MUTE) for TEA1062.



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FUNCTIONAL DESCRIPTION

Supplies V_{CC} , LN, SLPE, REG and STAB

Power for the IC and its peripheral circuits is usually obtained from the telephone line. The supply voltage is derived from the line via a dropping resistor and regulated by the IC. The supply voltage V_{CC} may also be used to supply external circuits e.g. dialling and control circuits.

Decoupling of the supply voltage is performed by a capacitor between V_{CC} and V_{EE} . The internal voltage regulator is decoupled by a capacitor between REG and V_{EE} .

The DC current flowing into the set is determined by the exchange supply voltage V_{exch} , the feeding bridge resistance R_{exch} and the DC resistance of the telephone line R_{line} .

The circuit has an internal current stabilizer operating at a level determined by a 3.6 k Ω resistor connected between STAB and V_{EE} (see Fig.9). When the line current (I_{line}) is more than 0.5 mA greater than the sum of the IC supply current (I_{CC}) and the current drawn by the peripheral circuitry connected to V_{CC} (I_p) the excess current is shunted to V_{EE} via LN.

The regulated voltage on the line terminal (V_{LN}) can be calculated as:

$$V_{LN} = V_{ref} + I_{SLPE} \times R_9$$

$$V_{LN} = V_{ref} + \{(I_{line} - I_{CC} - 0.5 \times 10^{-3} \text{ A}) - I_p\} \times R_9$$

V_{ref} is an internally generated temperature compensated reference voltage of 3.7 V and R_9 is an external resistor connected between SLPE and V_{EE} .

In normal use the value of R_9 would be 20 Ω .

Changing the value of R_9 will also affect microphone gain, DTMF gain, gain control characteristics, sidetone level, maximum output swing on LN and the DC characteristics (especially at the lower voltages).

Under normal conditions, when $I_{SLPE} \gg I_{CC} + 0.5 \text{ mA} + I_p$, the static behaviour of the circuit is that of a 3.7 V regulator diode with an internal resistance equal to that of R_9 . In the audio frequency range the dynamic impedance is largely determined by R_1 . Fig.3 shows the equivalent impedance of the circuit.

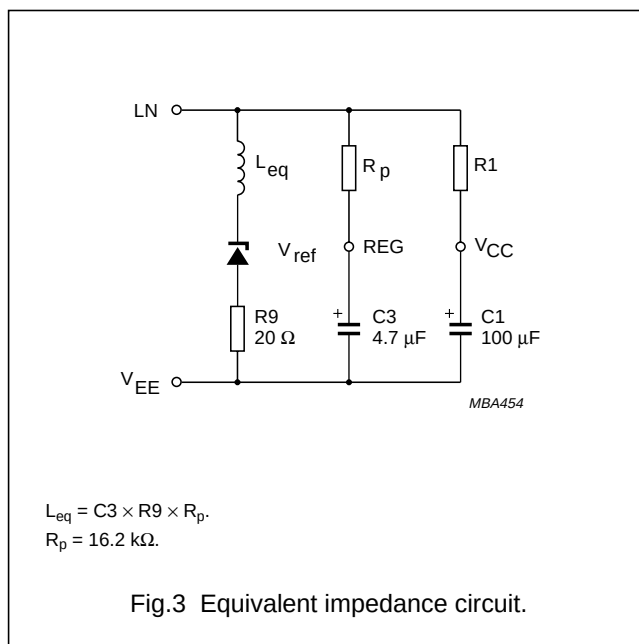


Fig.3 Equivalent impedance circuit.

At line currents below 9 mA the internal reference voltage is automatically adjusted to a lower value (typically 1.6 V at 1 mA). This means that more sets can be operated in parallel with DC line voltages (excluding the polarity guard) down to an absolute minimum voltage of 1.6 V. At line currents below 9 mA the circuit has limited sending and receiving levels. The internal reference voltage can be adjusted by means of an external resistor (R_{VA}). This resistor when connected between LN and REG will decrease the internal reference voltage and when connected between REG and SLPE will increase the internal reference voltage.

Current (I_p) available from V_{CC} for peripheral circuits depends on the external components used. Fig.10 shows this current for $V_{CC} > 2.2 \text{ V}$. If MUTE is LOW (TEA1062) or MUTE is HIGH (TEA1062A) when the receiving amplifier is driven, the available current is further reduced. Current availability can be increased by connecting the supply IC (TEA1081) in parallel with R_1 as shown in Fig.19 and Fig.20, or by increasing the DC line voltage by means of an external resistor (R_{VA}) connected between REG and SLPE (Fig.18).

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Microphone inputs MIC+ and MIC– and gain pins GAS1 and GAS2

The circuit has symmetrical microphone inputs. Its input impedance is $64\text{ k}\Omega$ ($2 \times 32\text{ k}\Omega$) and its voltage gain is typically 52 dB (when $R7 = 68\text{ k}\Omega$, see Figures 14 and 15). Dynamic, magnetic, piezoelectric or electret (with built-in FET source followers) can be used. Microphone arrangements are illustrated in Fig.11.

The gain of the microphone amplifier can be adjusted between 44 dB and 52 dB to suit the sensitivity of the transducer in use. The gain is proportional to the value of $R7$ which is connected between GAS1 and GAS2.

Stability is ensured by two external capacitors, $C6$ connected between GAS1 and SLPE and $C8$ connected between GAS1 and V_{EE} . The value of $C6$ is 100 pF but this may be increased to obtain a first-order low-pass filter. The value of $C8$ is 10 times the value of $C6$. The cut-off frequency corresponds to the time constant $R7 \times C6$.

Input MUTE (TEA1062)

When MUTE is HIGH the DTMF input is enabled and the microphone and receiving amplifier inputs are inhibited. The reverse is true when MUTE is LOW or open-circuit. MUTE switching causes only negligible clicking on the line and earpiece output. If the number of parallel sets in use causes a drop in line current to below 6 mA the speech amplifiers remain active independent to the DC level applied to the MUTE input.

Input $\overline{\text{MUTE}}$ (TEA1062A)

When $\overline{\text{MUTE}}$ is LOW or open-circuit, the DTMF input is enabled and the microphone and receiving amplifier inputs are inhibited. The reverse is true when $\overline{\text{MUTE}}$ is HIGH. $\overline{\text{MUTE}}$ switching causes only negligible clicking on the line and earpiece output. If the number of parallel sets in use causes a drop in line current to below 6 mA the DTMF amplifier becomes active independent to the DC level applied to the $\overline{\text{MUTE}}$ input.

Dual-tone multi-frequency input DTMF

When the DTMF input is enabled dialling tones may be sent on to the line. The voltage gain from DTMF to LN is typically 25.5 dB (when $R7 = 68\text{ k}\Omega$) and varies with $R7$ in the same way as the microphone gain. The signalling tones can be heard in the earpiece at a low level (confidence tone).

Receiving amplifier IR, QR and GAR

The receiving amplifier has one input (IR) and a non-inverting output (QR). Earpiece arrangements are illustrated in Fig.12. The IR to QR gain is typically 31 dB (when $R4 = 100\text{ k}\Omega$). It can be adjusted between 20 and 31 dB to match the sensitivity of the transducer in use. The gain is set with the value of $R4$ which is connected between GAR and QR. The overall receive gain, between LN and QR, is calculated by subtracting the anti-sidetone network attenuation (32 dB) from the amplifier gain. Two external capacitors, $C4$ and $C7$, ensure stability. $C4$ is normally 100 pF and $C7$ is 10 times the value of $C4$. The value of $C4$ may be increased to obtain a first-order low-pass filter. The cut-off frequency will depend on the time constant $R4 \times C4$.

The output voltage of the receiving amplifier is specified for continuous-wave drive. The maximum output voltage will be higher under speech conditions where the peak to RMS ratio is higher.

Automatic Gain Control input AGC

Automatic line loss compensation is achieved by connecting a resistor ($R6$) between AGC and V_{EE} .

The automatic gain control varies the gain of the microphone amplifier and the receiving amplifier in accordance with the DC line current. The control range is 5.8 dB which corresponds to a line length of 5 km for a 0.5 mm diameter twisted-pair copper cable with a DC resistance of $176\text{ }\Omega/\text{km}$ and average attenuation of 1.2 dB/km). Resistor $R6$ should be chosen in accordance with the exchange supply voltage and its feeding bridge resistance (see Fig.13 and Table 1). The ratio of start and stop currents of the AGC curve is independent of the value of $R6$. If no automatic line-loss compensation is required the AGC pin may be left open-circuit. The amplifiers, in this condition, will give their maximum specified gain.

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Sidetone suppression

The anti-sidetone network, $R1/Z_{line}$, $R2$, $R3$, $R8$, $R9$ and Z_{bal} , (see Fig.4) suppresses the transmitted signal in the earpiece. Maximum compensation is obtained when the following conditions are fulfilled:

$$R9 \times R2 = R1 \times \left(R3 + \frac{R8 \times Z_{bal}}{R8 + Z_{bal}} \right) \quad (1)$$

$$\frac{Z_{bal}}{Z_{bal} + R8} = \frac{Z_{line}}{Z_{line} + R1} \quad (2)$$

If fixed values are chosen for $R1$, $R2$, $R3$ and $R9$, then condition (1) will always be fulfilled when $|R8/Z_{bal}| \ll R3$.

To obtain optimum sidetone suppression, condition (2) has to be fulfilled which results in:

$$Z_{bal} = \frac{R8}{R1} \times Z_{line} = k \times Z_{line}$$

Where k is a scale factor; $k = \frac{R8}{R1}$

The scale factor k , dependent on the value of $R8$, is chosen to meet the following criteria:

- compatibility with a standard capacitor from the E6 or E12 range for Z_{bal}
- $|Z_{bal}/R8| \ll R3$ fulfilling condition (a) and thus ensuring correct anti-sidetone bridge operation
- $|Z_{bal} + R8| \gg R9$ to avoid influencing the transmit gain.

In practise Z_{line} varies considerably with the line type and length. The value chosen for Z_{bal} should therefore be for an average line length thus giving optimum setting for short or long lines.

EXAMPLE

The balance impedance Z_{bal} at which the optimum suppression is present can be calculated by:

Suppose $Z_{line} = 210 \Omega + (1265 \Omega/140 \text{ nF})$ representing a 5 km line of 0.5 mm diameter, copper, twisted-pair cable matched to 600 Ω (176 Ω/km ; 38 nF/km).

When $k = 0.64$ then $R8 = 390 \Omega$;
 $Z_{bal} = 130 \Omega + (820 \Omega/220 \text{ nF})$.

The anti-sidetone network for the TEA1060 family shown in Fig.4 attenuates the signal received from the line by 32 dB before it enters the receiving amplifier. The attenuation is almost constant over the whole audio-frequency range.

Figure 5 shows a conventional Wheatstone bridge anti-sidetone circuit that can be used as an alternative. Both bridge types can be used with either resistive or complex set impedances. (More information on the balancing of anti-sidetone bridges can be obtained in our publication "Applications Handbook for Wired telecom systems, IC03b", order number 9397 750 00811.)

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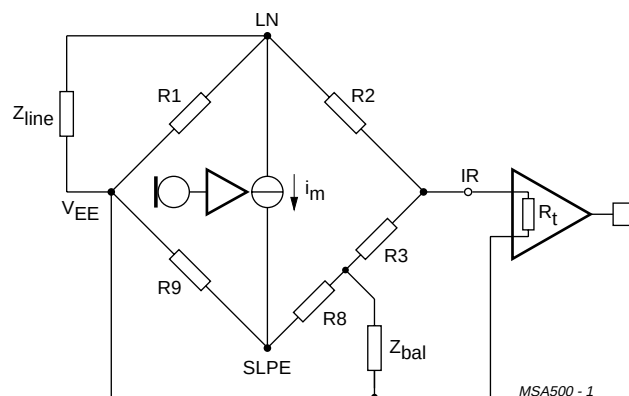


Fig.4 Equivalent circuit of TEA1060 family anti-sidetone bridge.

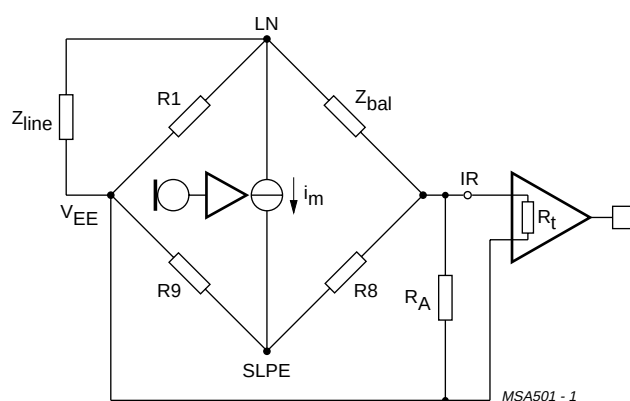


Fig.5 Equivalent circuit of an anti-sidetone network in a Wheatstone bridge configuration.

Low voltage transmission circuits with dialler interface

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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{LN}	positive continuous line voltage		–	12	V
$V_{LN(R)}$	repetitive line voltage during switch-on or line interruption		–	13.2	V
$V_{LN(RM)}$	repetitive peak line voltage for a 1 ms pulse per 5 s	$R_9 = 20\ \Omega$; $R_{10} = 13\ \Omega$; see Fig.18	–	28	V
I_{line}	line current	$R_9 = 20\ \Omega$; note 1	–	140	mA
V_I	input voltage on all other pins	positive input voltage	–	$V_{CC} + 0.7$	V
		negative input voltage	–	–0.7	V
P_{tot}	total power dissipation	$R_9 = 20\ \Omega$; note 2	–		
	TEA1062; TEA1062A		–	666	mW
	TEA1062M1; TEA1062AM1		–	617	mW
	TEA1062T; TEA1062AT		–	454	mW
T_{amb}	operating ambient temperature		–25	+75	°C
T_{stg}	storage temperature		–40	+125	°C
T_j	junction temperature		–	125	°C

Notes

- Mostly dependent on the maximum required T_{amb} and on the voltage between LN and SLPE (see Figs 6, 7 and 8).
- Calculated for the maximum ambient temperature specified ($T_{amb} = 75\ ^\circ\text{C}$) and a maximum junction temperature of $125\ ^\circ\text{C}$.

HANDLING

This device meets class 2 ESD test requirements [Human Body Model (HBM)], in accordance with "MIL STD 883C - method 3015".

THERMAL CHARACTERISTICS

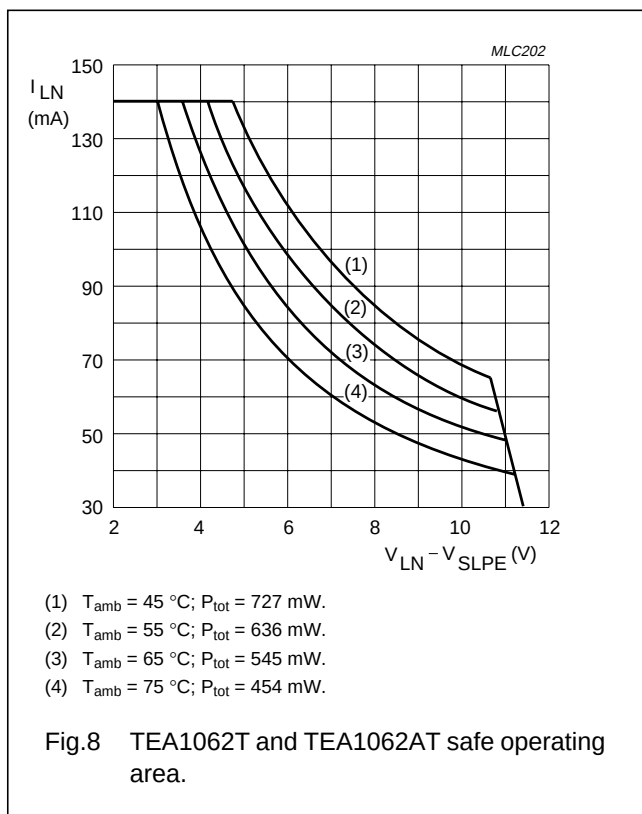
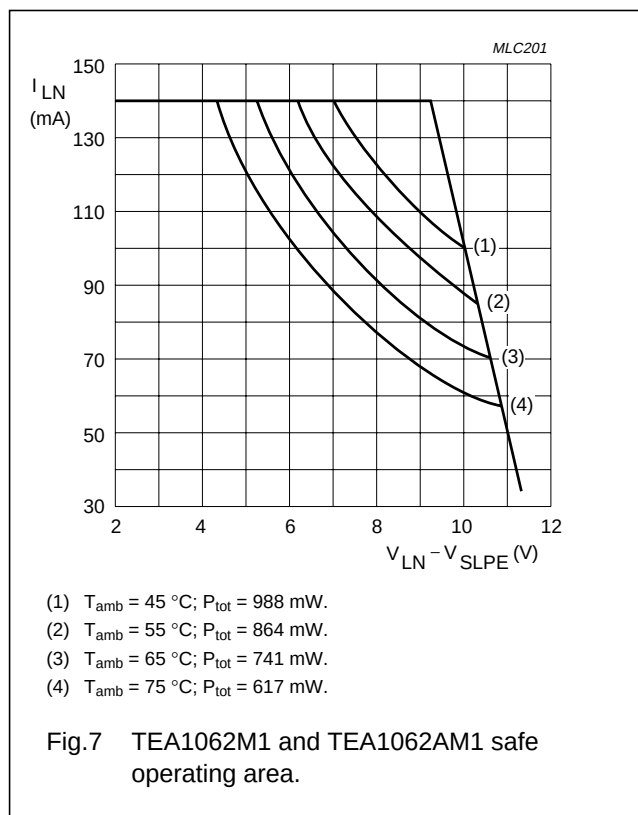
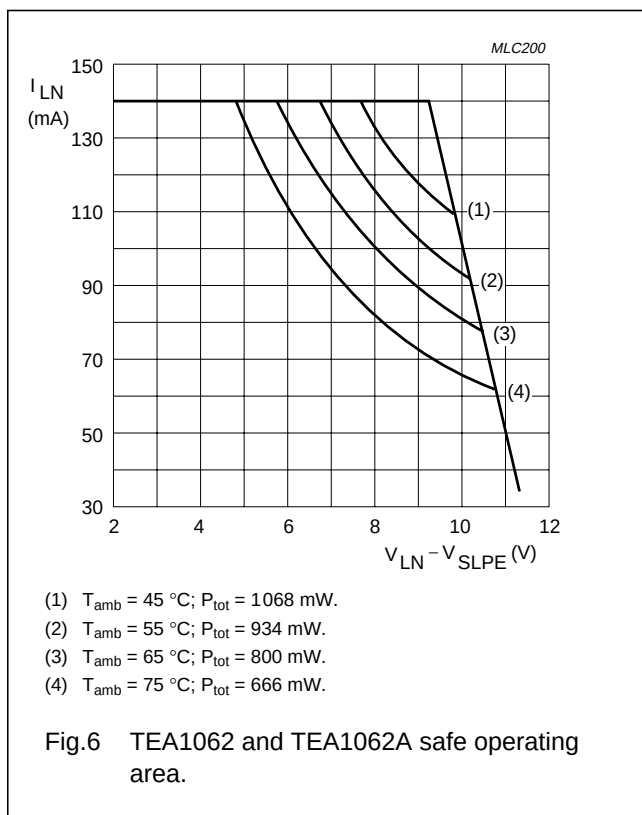
SYMBOL	PARAMETER	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient in free air		
	TEA1062; TEA1062A	75	K/W
	TEA1062M1; TEA1062AM1	81	K/W
	TEA1062T; TEA1062AT (note 1)	110	K/W

Note

- Mounted on glass epoxy board $28.5 \times 19.1 \times 1.5\ \text{mm}$.

Low voltage transmission circuits with dialler interface

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Low voltage transmission circuits with dialler interface

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CHARACTERISTICS

 $I_{line} = 11$ to 140 mA; $V_{EE} = 0$ V; $f = 800$ Hz; $T_{amb} = 25$ °C; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Supplies LN and V_{CC} (pins 1 and 13)						
V_{LN}	voltage drop over circuit between LN and V_{EE}	MIC inputs open-circuit				
		$I_{line} = 1$ mA	–	1.6	–	V
		$I_{line} = 4$ mA	–	1.9	–	V
		$I_{line} = 15$ mA	3.55	4.0	4.25	V
		$I_{line} = 100$ mA	4.9	5.7	6.5	V
		$I_{line} = 140$ mA	–	–	7.5	V
$\Delta V_{LN}/\Delta T$	variation with temperature	$I_{line} = 15$ mA	–	–0.3	–	mV/K
V_{LN}	voltage drop over circuit between LN and V_{EE} with external resistor R_{VA}	$I_{line} = 15$ mA				
		R_{VA} (LN to REG) = 68 k Ω	–	3.5	–	V
		R_{VA} (REG to SLPE) = 39 k Ω	–	4.5	–	V
I_{CC}	supply current	$V_{CC} = 2.8$ V	–	0.9	1.35	mA
V_{CC}	supply voltage available for peripheral circuitry TEA1062	$I_{line} = 15$ mA; MUTE = HIGH				
		$I_p = 1.2$ mA	2.2	2.7	–	V
		$I_p = 0$ mA	–	3.4	–	V
V_{CC}	supply voltage available for peripheral circuitry TEA1062A	$I_{line} = 15$ mA; MUTE = LOW				
		$I_p = 1.2$ mA	2.2	2.7	–	V
		$I_p = 0$ mA	–	3.4	–	V
Microphone inputs MIC– and MIC+ (pins 6 and 7)						
$ Z_i $	input impedance					
	differential	between MIC– and MIC+	–	64	–	k Ω
	single-ended	MIC– or MIC+ to V_{EE}	–	32	–	k Ω
CMRR	common mode rejection ratio		–	82	–	dB
G_v	voltage gain MIC+ or MIC– to LN	$I_{line} = 15$ mA; $R_7 = 68$ k Ω	50.5	52.0	53.5	dB
ΔG_{vf}	gain variation with frequency referenced to 800 Hz	$f = 300$ and 3400 Hz	–	± 0.2	–	dB
ΔG_{vT}	gain variation with temperature referenced to 25 °C	without R_6 ; $I_{line} = 50$ mA; $T_{amb} = -25$ and $+75$ °C	–	± 0.2	–	dB
DTMF input (pin 11)						
$ Z_i $	input impedance		–	20.7	–	k Ω
G_v	voltage gain from DTMF to LN	$I_{line} = 15$ mA; $R_7 = 68$ k Ω	24.0	25.5	27.0	dB
ΔG_{vf}	gain variation with frequency referenced to 800 Hz	$f = 300$ and 3400 Hz	–	± 0.2	–	dB
ΔG_{vT}	gain variation with temperature referenced to 25 °C	$I_{line} = 50$ mA; $T_{amb} = -25$ and $+75$ °C	–	± 0.2	–	dB

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SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Gain adjustment inputs GAS1 and GAS2 (pins 2 and 3)						
ΔG_v	transmitting amplifier gain variation by adjustment of R7 between GAS1 and GAS2		-8	-	0	dB
Sending amplifier output LN (pin 1)						
$V_{LN(rms)}$	output voltage (RMS value)	THD = 10% $I_{line} = 4 \text{ mA}$ $I_{line} = 15 \text{ mA}$	- 1.7	0.8 2.3	- -	V V
$V_{no(rms)}$	noise output voltage (RMS value)	$I_{line} = 15 \text{ mA}$; R7 = 68 k Ω ; 200 Ω between MIC- and MIC+; psophometrically weighted (P53 curve)	-	-69	-	dBmp
Receiving amplifier input IR (pin 10)						
$ Z_i $	input impedance		-	21	-	k Ω
Receiving amplifier output QR (pin 4)						
$ Z_o $	output impedance		-	4	-	Ω
G_v	voltage gain from IR to QR	$I_{line} = 15 \text{ mA}$; $R_L = 300 \text{ }\Omega$ (from pin 9 to pin 4)	29.5	31	32.5	dB
ΔG_{vf}	gain variation with frequency referenced to 800 Hz	f = 300 and 3400 Hz	-	± 0.2	-	dB
ΔG_{vT}	gain variation with temperature referenced to 25 °C	without R6; $I_{line} = 50 \text{ mA}$; $T_{amb} = -25 \text{ and } +75 \text{ }^\circ\text{C}$	-	± 0.2	-	dB
$V_{o(rms)}$	output voltage (RMS value)	THD = 2%; sine wave drive; R4 = 100 k Ω ; $I_{line} = 15 \text{ mA}$; $I_p = 0 \text{ mA}$ $R_L = 150 \text{ }\Omega$ $R_L = 450 \text{ }\Omega$	0.22 0.3	0.33 0.48	- -	V V
$V_{o(rms)}$	output voltage (RMS value)	THD = 10%; R4 = 100 k Ω ; $R_L = 150 \text{ }\Omega$; $I_{line} = 4 \text{ mA}$	-	15	-	mV
$V_{no(rms)}$	noise output voltage (RMS value)	$I_{line} = 15 \text{ mA}$; R4 = 100 k Ω ; IR open-circuit psophometrically weighted (P53 curve); $R_L = 300 \text{ }\Omega$	-	50	-	μV
Gain adjustment input GAR (pin 5)						
ΔG_v	receiving amplifier gain variation by adjustment of R4 between GAR and QR		-11	-	0	dB
Mute input (pin 12)						
V_{IH}	HIGH level input voltage		1.5	-	V_{CC}	V
V_{IL}	LOW level input voltage		-	-	0.3	V
I_{MUTE}	input current		-	8	15	μA

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SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Reduction of gain						
ΔG_v	MIC+ or MIC– to LN	MUTE = HIGH	–	70	–	dB
	TEA1062	MUTE = LOW	–	70	–	dB
G_v	voltage gain from DTMF to QR	R4 = 100 k Ω ; R _L = 300 Ω				
	TEA1062	MUTE = HIGH	–	–17	–	dB
	TEA1062A	MUTE = LOW	–	–17	–	dB
Automatic gain control input AGC (pin 15)						
ΔG_v	controlling the gain from IR to QR and the gain from MIC+, MIC– to LN gain control range	R6 = 110 k Ω (between AGC and V _{EE}) I _{line} = 70 mA	–	–5.8	–	dB
I _{lineH}	highest line current for maximum gain		–	23	–	mA
I _{lineL}	lowest line current for minimum gain		–	61	–	mA

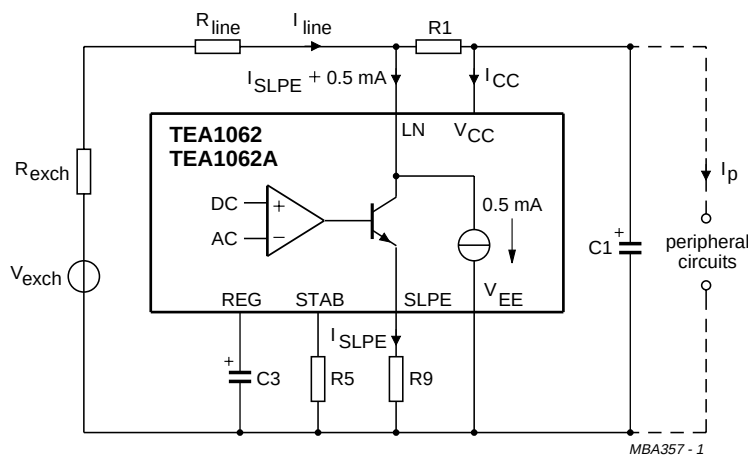
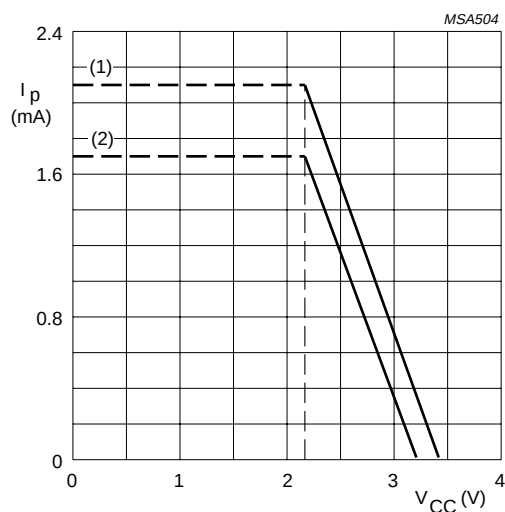


Fig.9 Supply arrangement.

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The supply possibilities can be increased by setting the voltage drop over the circuit V_{LN} to a higher value by resistor R_{VA} connected between REG and SLPE.

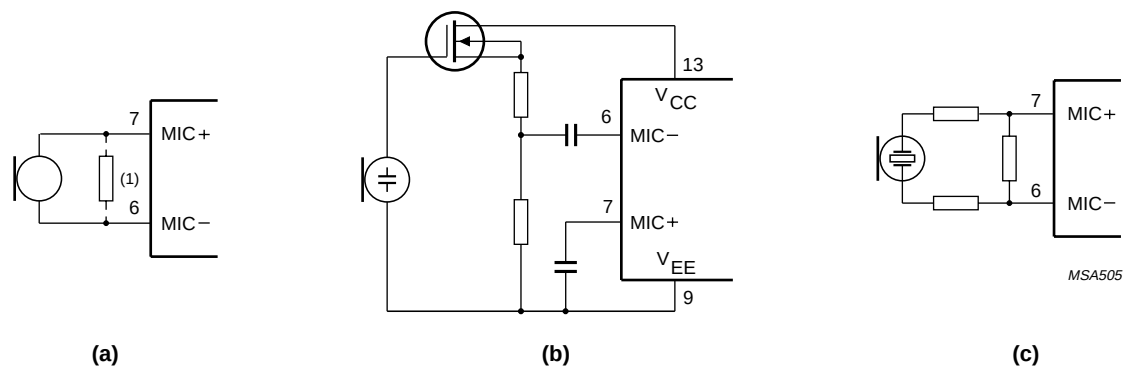
$V_{CC} > 2.2$ V; $I_{line} = 15$ mA at $V_{LN} = 4$ V; $R1 = 620\ \Omega$; $R9 = 20\ \Omega$.

- (1) $I_p = 2.1$ mA. Is valid when the receiving amplifier is not driven or when MUTE = HIGH (TEA1062), $\overline{\text{MUTE}} = \text{LOW}$ (TEA1062A).
- (2) $I_p = 1.7$ mA. Is valid when MUTE = LOW (TEA1062), $\overline{\text{MUTE}} = \text{HIGH}$ (TEA1062A) and the receiving amplifier is driven; $V_{o(rms)} = 150$ mV, $R_L = 150\ \Omega$.

Fig.10 Typical current I_p available from V_{CC} for peripheral circuitry.

Low voltage transmission circuits with dialler interface

TEA1062; TEA1062A



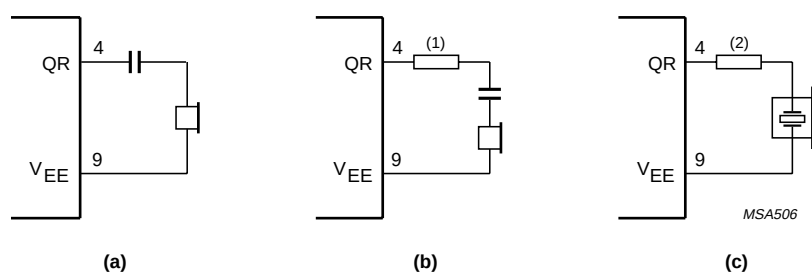
(a) Magnetic or dynamic microphone.

(b) Electret microphone.

(c) Piezoelectric microphone.

(1) Resistor may be connected to reduce the terminating impedance.

Fig.11 Alternative microphone arrangements.



(a) Dynamic earpiece.

(b) Magnetic earpiece.

(c) Piezoelectric earpiece.

(1) Resistor may be connected to prevent distortion (inductive load).

(2) Resistor is required to increase the phase margin (capacitive load).

Fig.12 Alternative receiver arrangements.

Low voltage transmission circuits with
dialler interface

TEA1062; TEA1062A

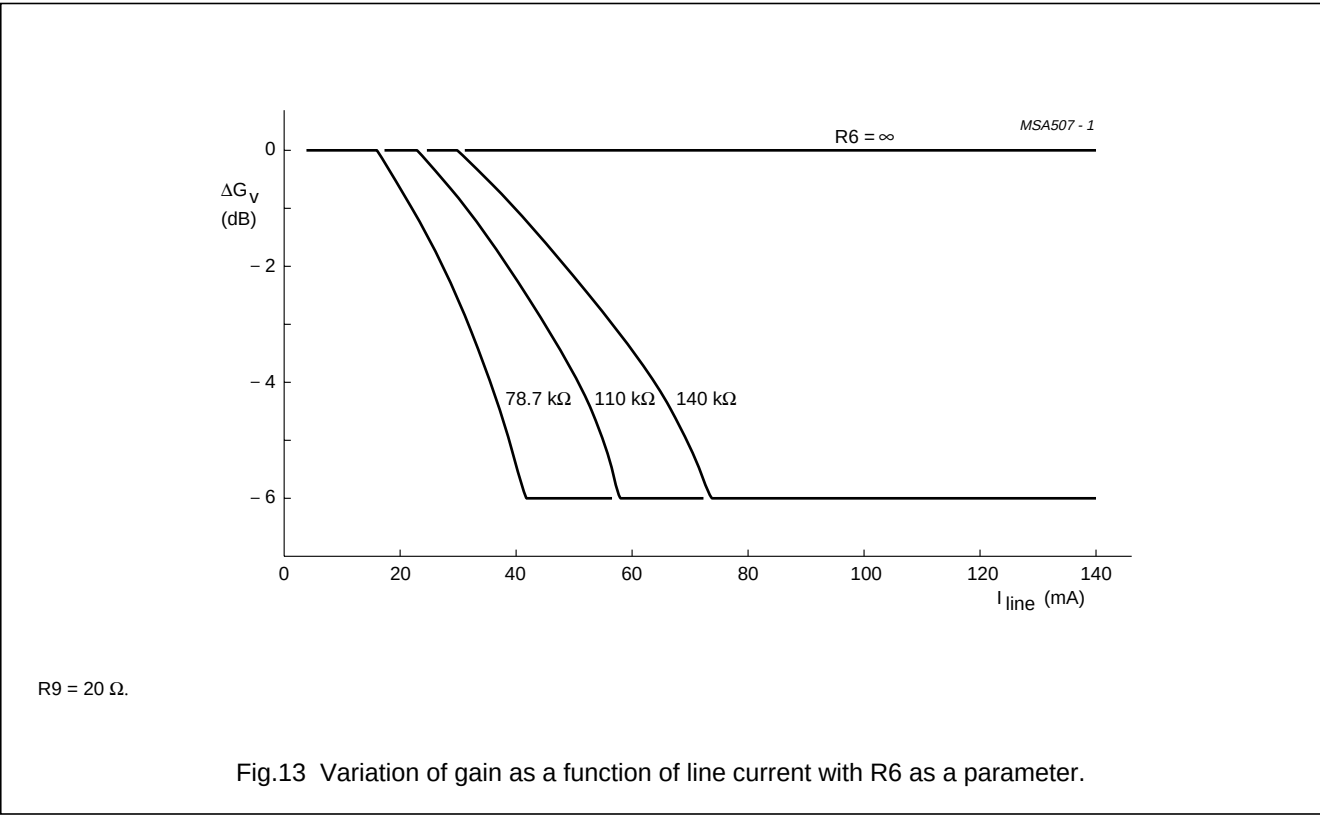
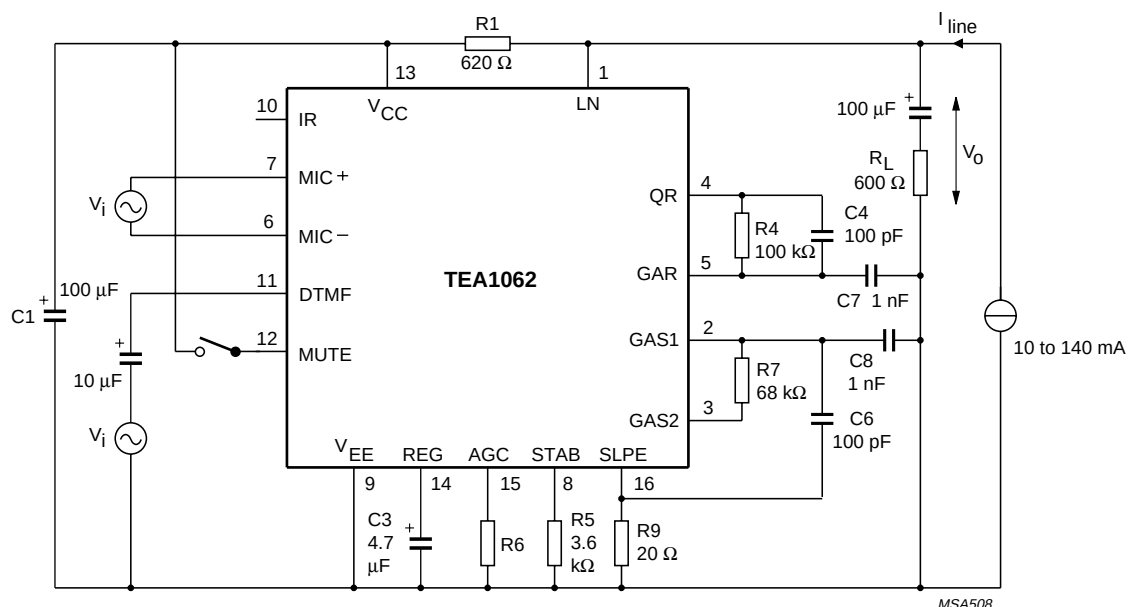


Table 1 Values of resistor R_6 for optimum line-loss compensation at various values of exchange supply voltage (V_{exch}) and exchange feeding bridge resistance (R_{exch}); $R_9 = 20 \Omega$.

V_{exch} (V)	R_6 (k Ω)			
	$R_{exch} = 400 \Omega$	$R_{exch} = 600 \Omega$	$R_{exch} = 800 \Omega$	$R_{exch} = 1000 \Omega$
36	100	78.7	—	—
48	140	110	93.1	82
60	—	—	120	102

Low voltage transmission circuits with dialler interface

TEA1062; TEA1062A



Voltage gain is defined as $G_v = 20 \log |V_o/V_i|$.

For measuring gain from MIC+ and MIC- the MUTE input should be LOW or open-circuit.

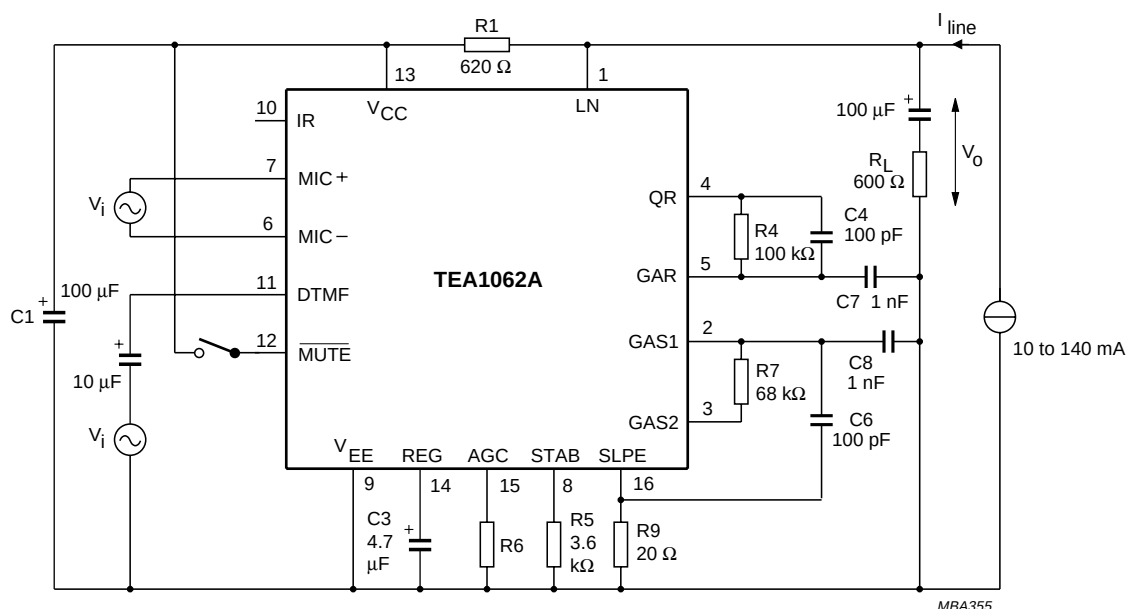
For measuring the DTMF input, the MUTE input should be HIGH.

Inputs not being tested should be open-circuit.

Fig.14 Test circuit for defining TEA1062 voltage gain of MIC+, MIC- and DTMF inputs.

Low voltage transmission circuits with dialler interface

TEA1062; TEA1062A



Voltage gain is defined as $G_v = 20 \log |V_o/V_i|$.

For measuring gain from MIC+ and MIC- the MUTE input should be HIGH.

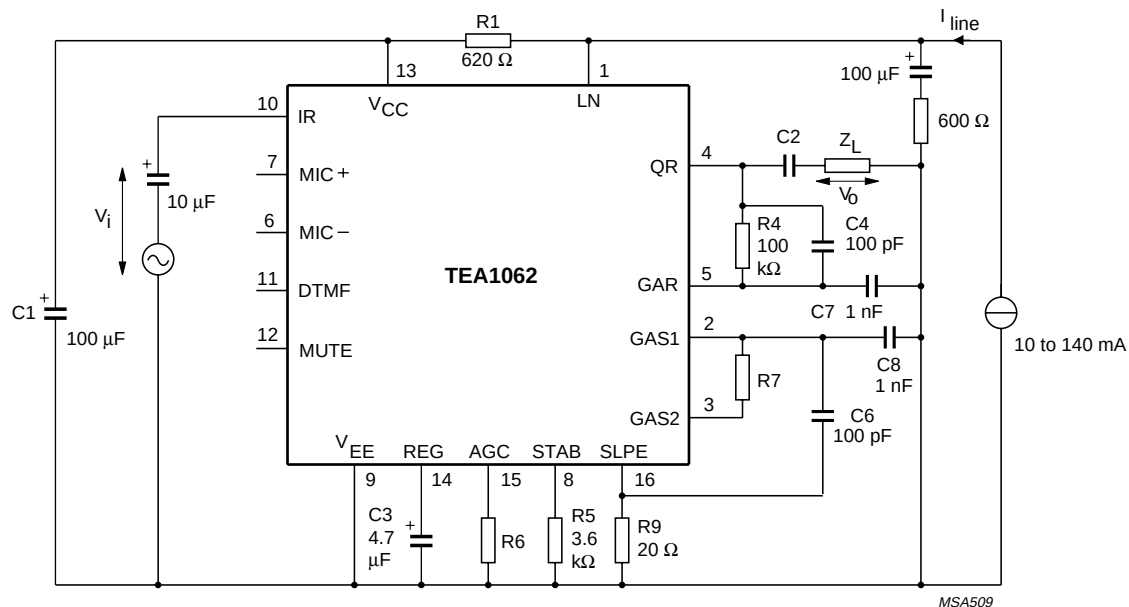
For measuring the DTMF input, the MUTE input should be LOW or open-circuit.

Inputs not being tested should be open-circuit.

Fig.15 Test circuit for defining TEA1062A voltage gain of MIC+, MIC- and DTMF inputs.

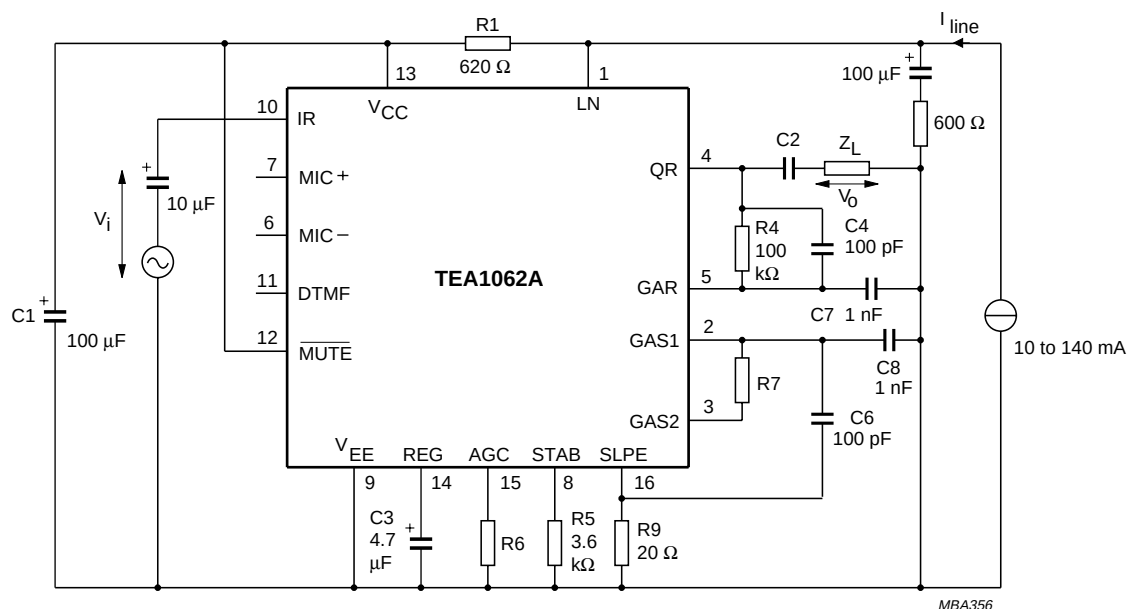
Low voltage transmission circuits with dialler interface

TEA1062; TEA1062A



Voltage gain is defined as $G_v = 20 \log |V_o/V_i|$.

Fig.16 Test circuit for defining TEA1062 voltage gain of the receiving amplifier.



Voltage gain is defined as $G_v = 20 \log |V_o/V_i|$.

Fig.17 Test circuit for defining TEA1062A voltage gain of the receiving amplifier.

Low voltage transmission circuits with dialler interface

TEA1062; TEA1062A

APPLICATION INFORMATION

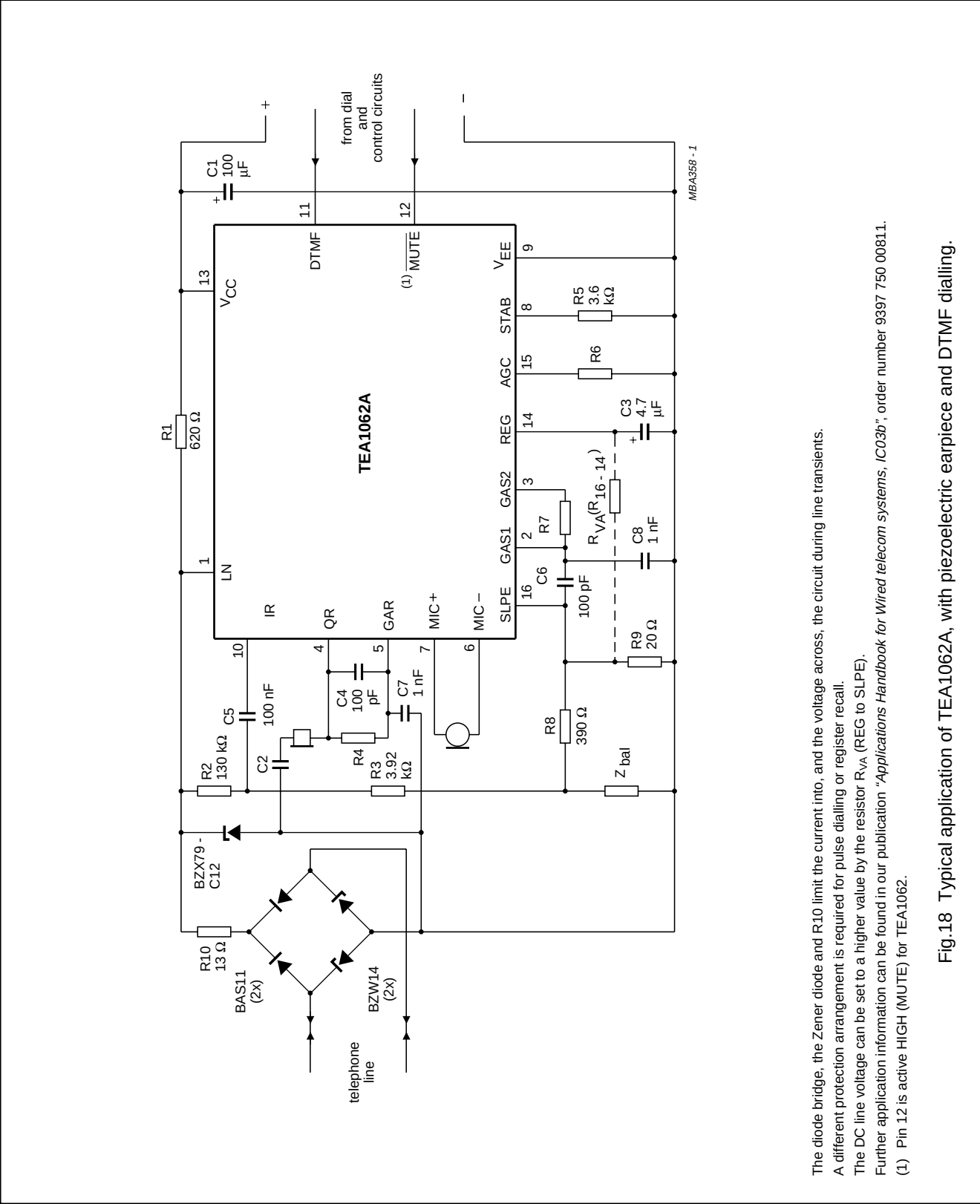
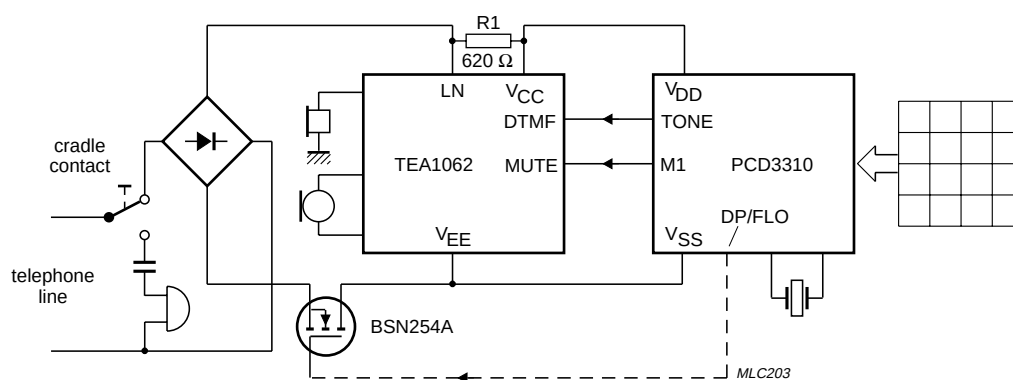


Fig.18 Typical application of TEA1062A, with piezoelectric earpiece and DTMF dialling.

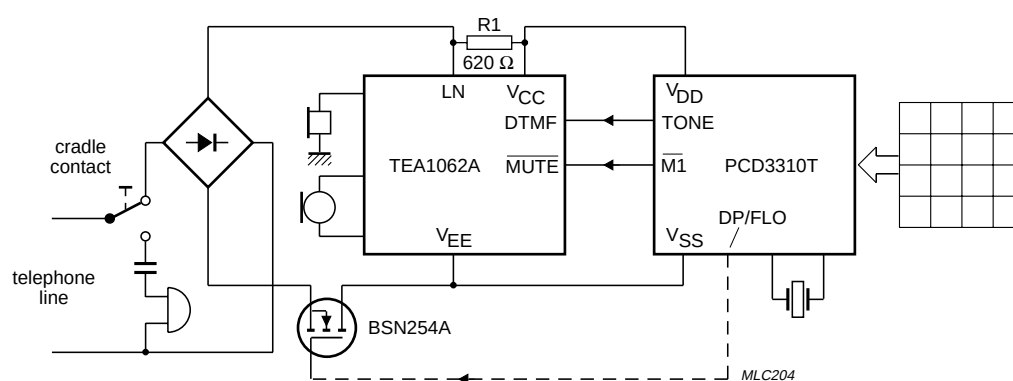
Low voltage transmission circuits with dialler interface

TEA1062; TEA1062A



(a) DTMF pulse set with CMOS bilingual dialling circuit PCD3310. The dashed line shows an optional flash (register recall by timed loop break).

Fig.19 Typical simplified application of the TEA1062.



(a) DTMF pulse set with CMOS bilingual dialling circuit PCD3310T. The dashed line shows an optional flash (register recall by timed loop break).

Fig.20 Typical simplified application of the TEA1062A.

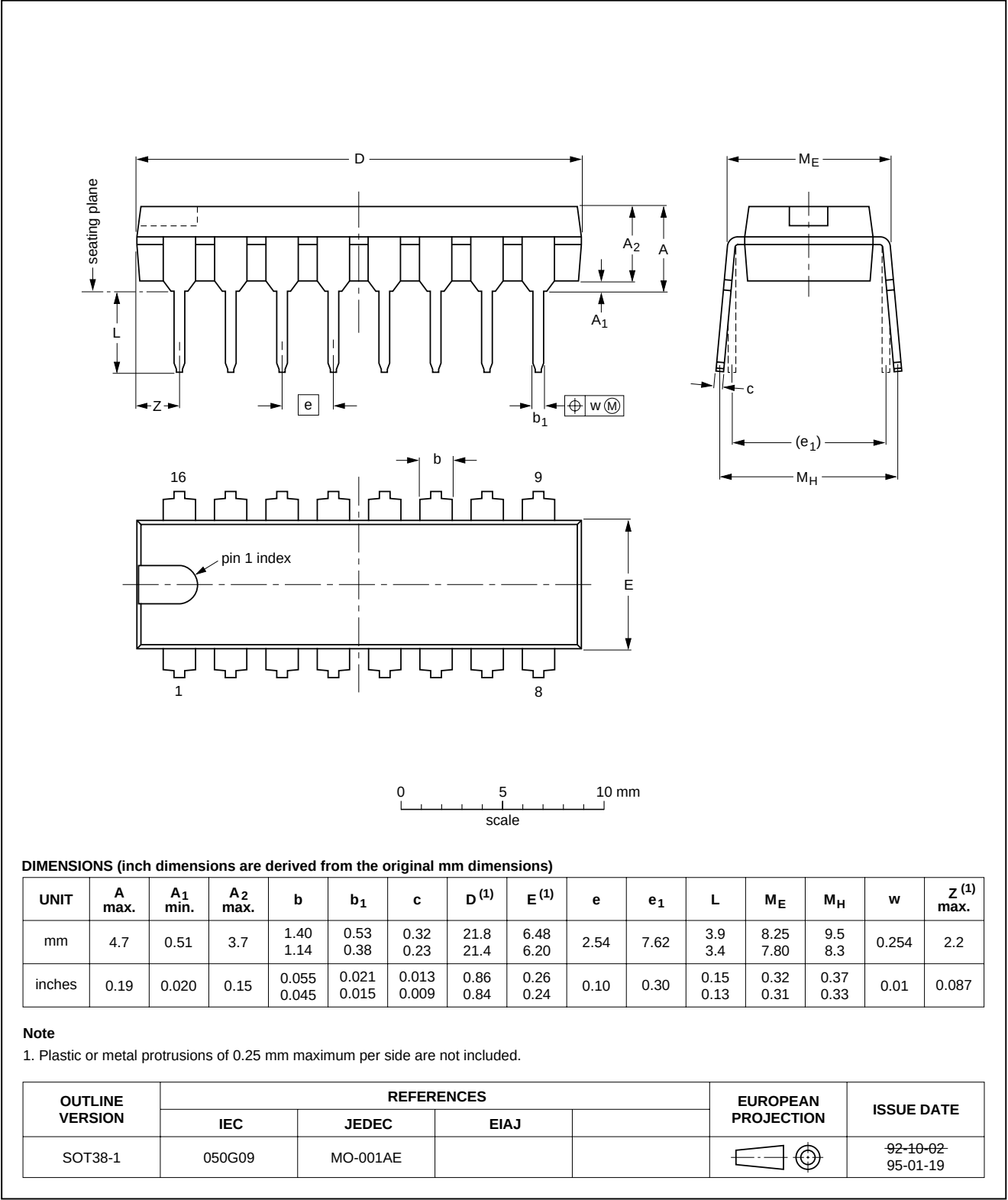
Low voltage transmission circuits with dialler interface

TEA1062; TEA1062A

PACKAGE OUTLINES

DIP16: plastic dual in-line package; 16 leads (300 mil); long body

SOT38-1

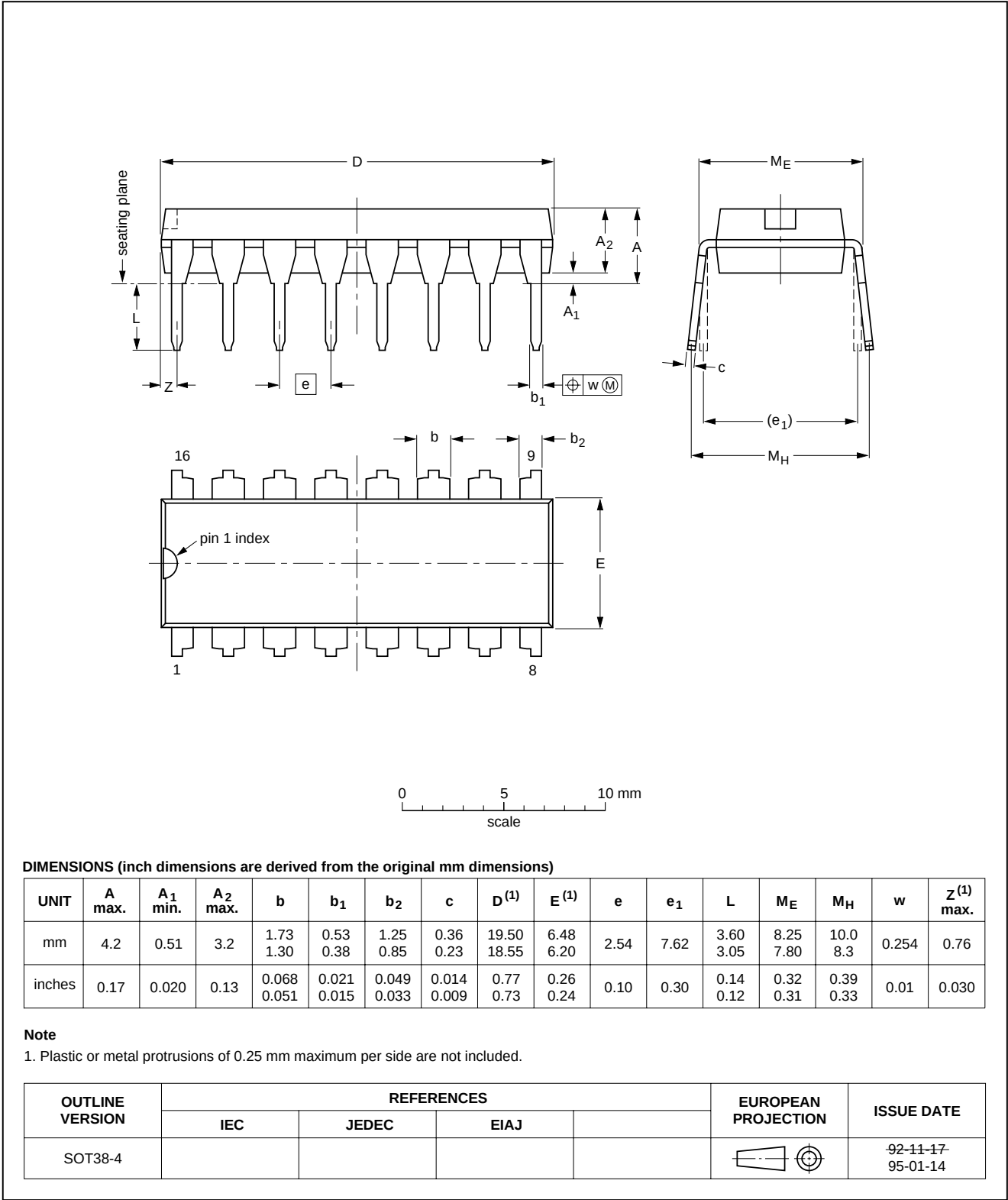


Low voltage transmission circuits with
dialler interface

TEA1062; TEA1062A

DIP16: plastic dual in-line package; 16 leads (300 mil)

SOT38-4

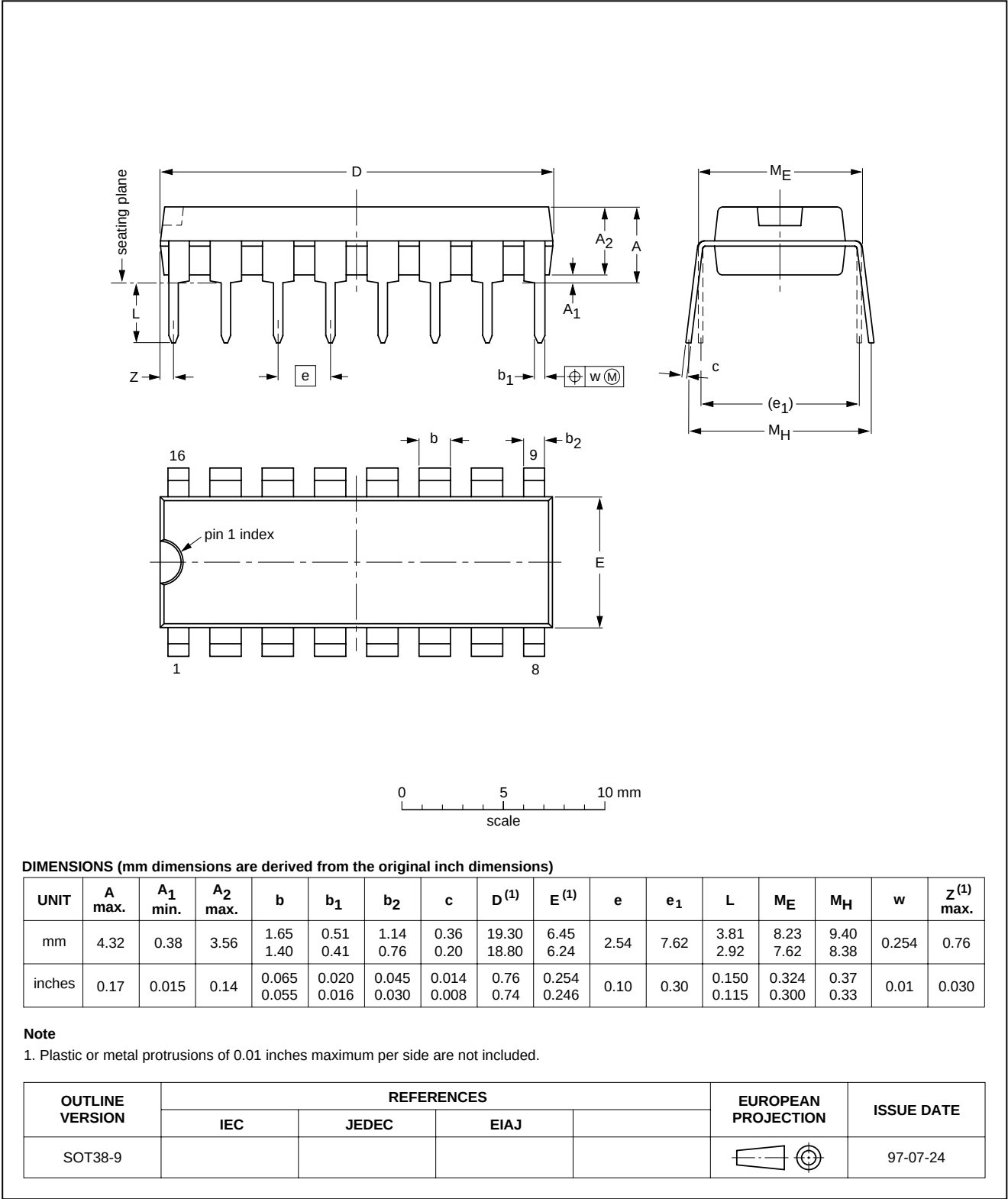


Low voltage transmission circuits with
dialler interface

TEA1062; TEA1062A

DIP16: plastic dual in-line package; 16 leads (300 mil)

SOT38-9

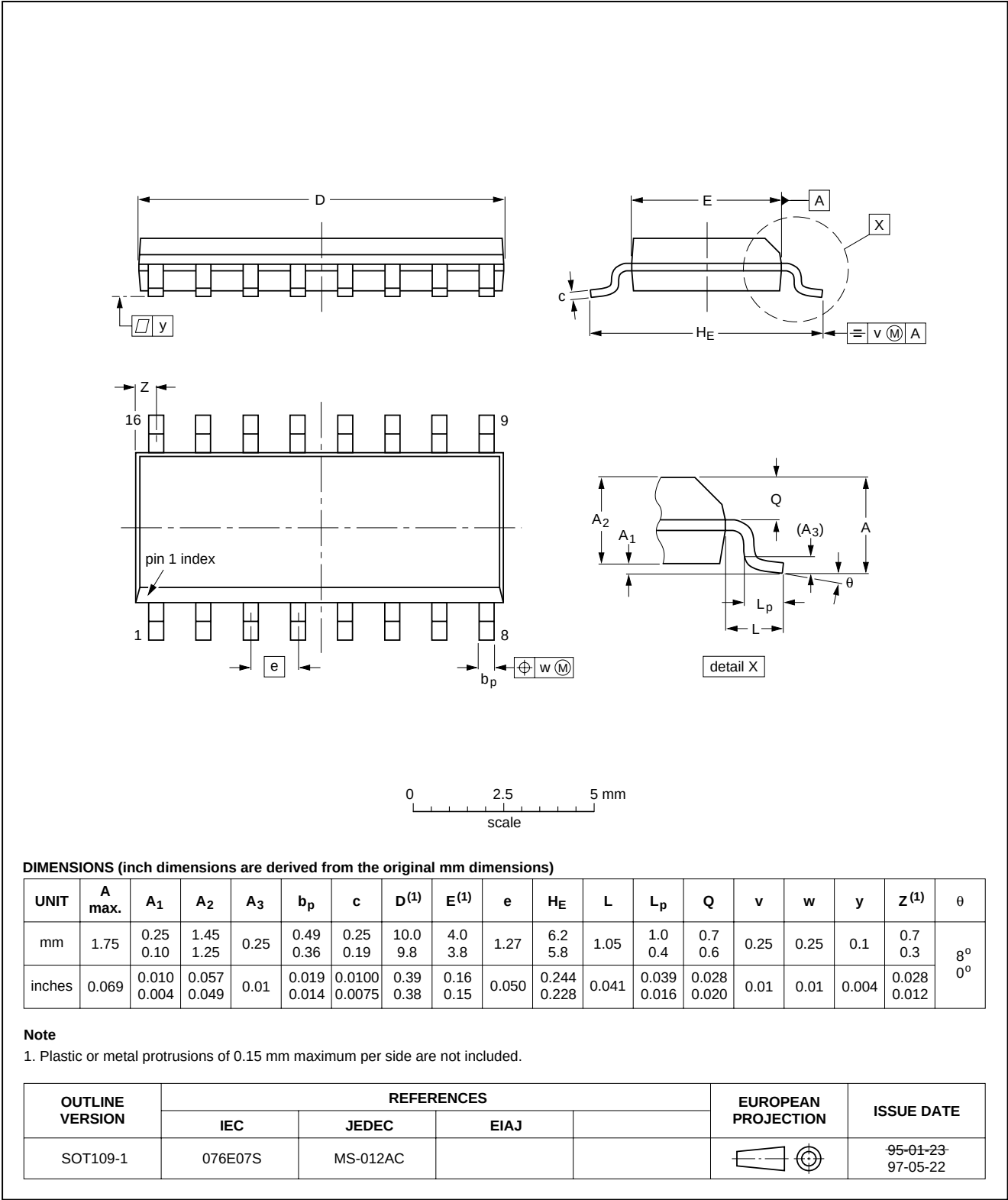


Low voltage transmission circuits with
dialler interface

TEA1062; TEA1062A

SO16: plastic small outline package; 16 leads; body width 3.9 mm

SOT109-1



Low voltage transmission circuits with dialler interface

TEA1062; TEA1062A

SOLDERING

Plastic dual in-line packages

BY DIP OR WAVE

The maximum permissible temperature of the solder is 260 °C; this temperature must not be in contact with the joint for more than 5 s. The total contact time of successive solder waves must not exceed 5 s.

The device may be mounted up to the seating plane, but the temperature of the plastic body must not exceed the specified storage maximum. If the printed-circuit board has been pre-heated, forced cooling may be necessary immediately after soldering to keep the temperature within the permissible limit.

REPAIRING SOLDERED JOINTS

Apply the soldering iron below the seating plane (or not more than 2 mm above it). If its temperature is below 300 °C, it must not be in contact for more than 10 s; if between 300 and 400 °C, for not more than 5 s.

Plastic small-outline packages

BY WAVE

During placement and before soldering, the component must be fixed with a droplet of adhesive. After curing the adhesive, the component can be soldered. The adhesive can be applied by screen printing, pin transfer or syringe dispensing.

Maximum permissible solder temperature is 260 °C, and maximum duration of package immersion in solder bath is 10 s, if allowed to cool to less than 150 °C within 6 s. Typical dwell time is 4 s at 250 °C.

A modified wave soldering technique is recommended using two solder waves (dual-wave), in which a turbulent wave with high upward pressure is followed by a smooth laminar wave. Using a mildly-activated flux eliminates the need for removal of corrosive residues in most applications.

BY SOLDER PASTE REFLOW

Reflow soldering requires the solder paste (a suspension of fine solder particles, flux and binding agent) to be applied to the substrate by screen printing, stencilling or pressure-syringe dispensing before device placement.

Several techniques exist for reflowing; for example, thermal conduction by heated belt, infrared, and vapour-phase reflow. Dwell times vary between 50 and 300 s according to method. Typical reflow temperatures range from 215 to 250 °C.

Preheating is necessary to dry the paste and evaporate the binding agent. Preheating duration: 45 min at 45 °C.

REPAIRING SOLDERED JOINTS (BY HAND-HELD SOLDERING IRON OR PULSE-HEATED SOLDER TOOL)

Fix the component by first soldering two, diagonally opposite, end pins. Apply the heating tool to the flat part of the pin only. Contact time must be limited to 10 s at up to 300 °C. When using proper tools, all other pins can be soldered in one operation within 2 to 5 s at between 270 and 320 °C. (Pulse-heated soldering is not recommended for SO packages.)

For pulse-heated solder tool (resistance) soldering of VSO packages, solder is applied to the substrate by dipping or by an extra thick tin/lead plating before package placement.

Low voltage transmission circuits with dialler interface

TEA1062; TEA1062A

DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

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Argentina: see South America

Australia: 34 Waterloo Road, NORTH RYDE, NSW 2113,
Tel. +61 2 9805 4455, Fax. +61 2 9805 4466

Austria: Computerstr. 6, A-1101 WIEN, P.O. Box 213,
Tel. +43 1 60 101, Fax. +43 1 60 101 1210

Belarus: Hotel Minsk Business Center, Bld. 3, r. 1211, Volodarski Str. 6,
220050 MINSK, Tel. +375 172 200 733, Fax. +375 172 200 773

Belgium: see The Netherlands

Brazil: see South America

Bulgaria: Philips Bulgaria Ltd., Energoproject, 15th floor,
51 James Bourchier Blvd., 1407 SOFIA,
Tel. +359 2 689 211, Fax. +359 2 689 102

Canada: PHILIPS SEMICONDUCTORS/COMPONENTS,
Tel. +1 800 234 7381

China/Hong Kong: 501 Hong Kong Industrial Technology Centre,
72 Tat Chee Avenue, Kowloon Tong, HONG KONG,
Tel. +852 2319 7888, Fax. +852 2319 7700

Colombia: see South America

Czech Republic: see Austria

Denmark: Prags Boulevard 80, PB 1919, DK-2300 COPENHAGEN S,
Tel. +45 32 88 2636, Fax. +45 31 57 1949

Finland: Sinikalliontie 3, FIN-02630 ESPOO,
Tel. +358 9 615800, Fax. +358 9 61580/xxx

France: 4 Rue du Port-aux-Vins, BP317, 92156 SURESNES Cedex,
Tel. +33 1 40 99 6161, Fax. +33 1 40 99 6427

Germany: Hammerbrookstraße 69, D-20097 HAMBURG,
Tel. +49 40 23 53 60, Fax. +49 40 23 536 300

Greece: No. 15, 25th March Street, GR 17778 TAVROS/ATHENS,
Tel. +30 1 4894 339/239, Fax. +30 1 4814 240

Hungary: see Austria

India: Philips INDIA Ltd, Shivsagar Estate, A Block, Dr. Annie Besant Rd.
Worli, MUMBAI 400 018, Tel. +91 22 4938 541, Fax. +91 22 4938 722

Indonesia: see Singapore

Ireland: Newstead, Clonskeagh, DUBLIN 14,
Tel. +353 1 7640 000, Fax. +353 1 7640 200

Israel: RAPAC Electronics, 7 Kehilat Saloniki St, TEL AVIV 61180,
Tel. +972 3 645 0444, Fax. +972 3 649 1007

Italy: PHILIPS SEMICONDUCTORS, Piazza IV Novembre 3,
20124 MILANO, Tel. +39 2 6752 2531, Fax. +39 2 6752 2557

Japan: Philips Bldg 13-37, Kohnan 2-chome, Minato-ku, TOKYO 108,
Tel. +81 3 3740 5130, Fax. +81 3 3740 5077

Korea: Philips House, 260-199 Itaewon-dong, Yongsan-ku, SEOUL,
Tel. +82 2 709 1412, Fax. +82 2 709 1415

Malaysia: No. 76 Jalan Universiti, 46200 PETALING JAYA, SELANGOR,
Tel. +60 3 750 5214, Fax. +60 3 757 4880

Mexico: 5900 Gateway East, Suite 200, EL PASO, TEXAS 79905,
Tel. +9-5 800 234 7381

Middle East: see Italy

Netherlands: Postbus 90050, 5600 PB EINDHOVEN, Bldg. VB,
Tel. +31 40 27 82785, Fax. +31 40 27 88399

New Zealand: 2 Wagener Place, C.P.O. Box 1041, AUCKLAND,
Tel. +64 9 849 4160, Fax. +64 9 849 7811

Norway: Box 1, Manglerud 0612, OSLO,
Tel. +47 22 74 8000, Fax. +47 22 74 8341

Philippines: Philips Semiconductors Philippines Inc.,
106 Valero St. Salcedo Village, P.O. Box 2108 MCC, MAKATI,
Metro MANILA, Tel. +63 2 816 6380, Fax. +63 2 817 3474

Poland: Ul. Lukiska 10, PL 04-123 WARSZAWA,
Tel. +48 22 612 2831, Fax. +48 22 612 2327

Portugal: see Spain

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Russia: Philips Russia, Ul. Usatcheva 35A, 119048 MOSCOW,
Tel. +7 095 247 9145, Fax. +7 095 247 9144

Singapore: Lorong 1, Toa Payoh, SINGAPORE 1231,
Tel. +65 350 2538, Fax. +65 251 6500

Slovakia: see Austria

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South Africa: S.A. PHILIPS Pty Ltd., 195-215 Main Road Martindale,
2092 JOHANNESBURG, P.O. Box 7430 Johannesburg 2000,
Tel. +27 11 470 5911, Fax. +27 11 470 5494

South America: Rua do Rocio 220, 5th floor, Suite 51,
04552-903 São Paulo, SÃO PAULO - SP, Brazil,
Tel. +55 11 821 2333, Fax. +55 11 829 1849

Spain: Balmes 22, 08007 BARCELONA,
Tel. +34 3 301 6312, Fax. +34 3 301 4107

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Taiwan: PHILIPS TAIWAN Ltd., 23-30F, 66,
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TAIPEI 100, Tel. +886 2 382 4443, Fax. +886 2 382 4444

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Turkey: Talatpasa Cad. No. 5, 80640 GÜLTEPE/ISTANBUL,
Tel. +90 212 279 2770, Fax. +90 212 282 6707

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252042 KIEV, Tel. +380 44 264 2776, Fax. +380 44 268 0461

United Kingdom: Philips Semiconductors Ltd., 276 Bath Road, Hayes,
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United States: 811 East Arques Avenue, SUNNYVALE, CA 94088-3409,
Tel. +1 800 234 7381

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Телефон: 8 (812) 309 58 32 (многоканальный)

Факс: 8 (812) 320-02-42

Электронная почта: org@eplast1.ru

Адрес: 198099, г. Санкт-Петербург, ул. Калинина, дом 2, корпус 4, литера А.